

MM54HC34/MM74HC34 Non-Inverter

General Description

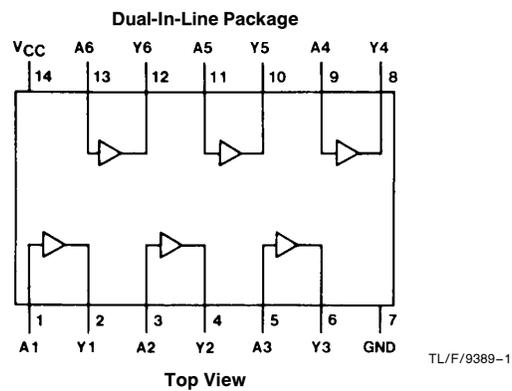
The MM54HC34/MM74HC34 are logic functions fabricated by using advanced silicon-gate CMOS technology which provides the inherent benefits of CMOS—low quiescent power and wide power supply range, but are functionally as well as pin-out compatible with standard DM54LS/74LS devices. The MM54HC34/MM74HC34 feature low power dis-

sipation and fast switching times. All inputs are protected from static discharge by internal diodes to V_{CC} and ground.

Features

- Fast switching: t_{PLH} , t_{PHL} = 10 ns (typ)
- High fanout: ≥ 10 LS loads

Connection Diagram



Order Number MM54HC34 or MM74HC34

MM54HC34/MM74HC34 Non-Inverter

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	-0.5V to +7.0V
DC Input Voltage (V_{IN})	-1.5V to V_{CC} + 1.5V
DC Output Voltage (V_{OUT})	-0.5V to V_{CC} + 0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{ICC})	±50 mA
Storage Temperature Range (T_{STG})	-65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times (t_r, t_f)			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$			Units	
				Typ	74HC $T_A = -40 \text{ to } +85^\circ C$	54HC $T_A = -55 \text{ to } +125^\circ C$		
V_{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	V	
			4.5V		3.15	3.15	V	
			6.0V		4.2	4.2	V	
V_{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	V	
			4.5V		1.35	1.35	V	
			6.0V		1.8	1.8	V	
V_{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IL}$ $ I_{OUT} \leq 20 \mu A$	2.0V	2.0	1.9	1.9	V	
			4.5V	4.5	4.4	4.4	V	
			6.0V	6.0	5.9	5.9	V	
		$V_{IN} = V_{IL}$ $ I_{OUT} \leq 4.0 \text{ mA}$ $ I_{OUT} \leq 5.2 \text{ mA}$	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ $ I_{OUT} \leq 20 \mu A$	2.0V	0	0.1	0.1	V	
			4.5V	0	0.1	0.1	V	
			6.0V	0	0.1	0.1	V	
		$V_{IN} = V_{IH}$ $ I_{OUT} \leq 4.0 \text{ mA}$ $ I_{OUT} \leq 5.2 \text{ mA}$	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		2.0	20	40	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating—plastic "N" package: -12 mW/°C from 65°C to 85°C, ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ± 10% the worst case output voltages (V_{OH} , and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 \text{ pF}, t_r = t_f = 6 \text{ ns}$

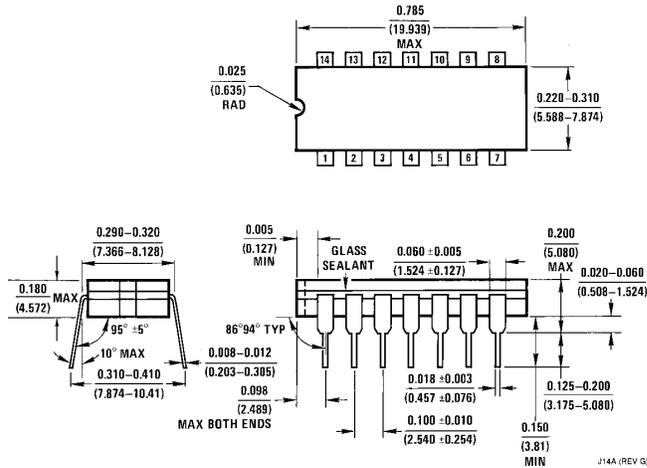
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay		10		ns

AC Electrical Characteristics $V_{CC} = 2.0V \text{ to } 6.0V, C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns}$ (unless otherwise specified)

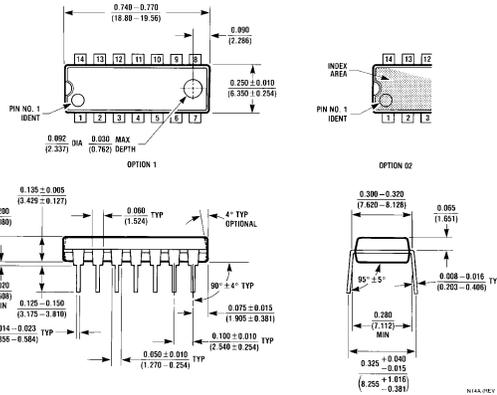
Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
						$T_A = -40^\circ C \text{ to } +85^\circ C$	$T_A = -55^\circ C \text{ to } +125^\circ C$	
Guaranteed Limits								
t_{PHL}, t_{PLH}	Minimum Propagation Delay		2.0V	30	80	100	120	ns
			4.5V	10	16	20	24	ns
			6.0V	8	14	17	20	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	50	75	95	110	ns
			4.5V	10	75	19	22	ns
			6.0V	8	13	16	19	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		26				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Physical Dimensions inches (millimeters)



14 Lead Cerdip (J)
Order Number MM54HC34J or MM74HC34J
NS Package Number J14A



14 Lead Molded Dip (N)
Order Number MM74HC34N
NS Package Number N14A

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

National Semiconductor Corporation
 1111 West Bardin Road
 Arlington, TX 76017
 Tel: 1(800) 272-9959
 Fax: 1(800) 737-7018

National Semiconductor Europe
 Fax: (+49) 0-180-530 85 86
 Email: cnjwge@tevm2.nsc.com
 Deutsch Tel: (+49) 0-180-530 85 85
 English Tel: (+49) 0-180-532 78 32
 Français Tel: (+49) 0-180-532 93 58
 Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
 19th Floor, Straight Block,
 Ocean Centre, 5 Canton Rd.
 Tsimshatsui, Kowloon
 Hong Kong
 Tel: (852) 2737-1600
 Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
 Tel: 81-043-299-2309
 Fax: 81-043-299-2408